

Analog Communication Laboratory Manual

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Chapter 1

Introduction to Analog Communication

[1]Communication is the transfer of information from one place to another. A bidirectional communication system operates in opposite directions. The receiver can respond to the sender. Radio communication uses electrical energy to transmit information. Because electrical energy travels almost as fast as light, radio communication is essentially instantaneous. A radio transmitter converts audio (sound) signals to electrical signals that are sent over wires or through space. A radio receiver converts the electromagnetic waves back to sound waves so that the information can be understood.

The transmitted information is the **intelligence signal** or **message signal**. Message signals are in the **Audio Frequency (AF)** range of low frequencies from about 20 Hz to 20 kHz.

The **Radio Frequency (RF)** is the carrier signal. Carrier signals have high frequencies that range from 10 kHz up to about 1000 GHz. A radio transmitter sends the low frequency message signal at the higher carrier signal frequency by combining the message signal with the carrier signal.

Modulation is the process of changing a characteristic of the carrier signal with the message signal. In the transmitter, the message signal modulates the carrier signal. The modulated carrier signal is sent to the receiver where **de-modulation** of the carrier occurs to recover the message signal.

IMPORTANT TERMS

- **Audio** - signals that a person can hear.
- **Electromagnetic waves** - the radiant energy produced by oscillation of an electric charge.
- **Intelligence signal** - any signal that contains information; it is also called the message signal.

- **Message signal** - any signal that contains information; it is also called the intelligence signal.
- **Audio Frequency (AF)** - frequencies that a person can hear. AF signals range from about 20 Hz to 20 kHz.
- **Radio Frequency (RF)** - the transmission frequency of electromagnetic (radio) signals. RF frequencies are from about 300 kHz to the 1,000,000 kHz range.
- **Carrier signal** - a single, high-frequency signal that can be modulated by a message signal and transmitted.
- **Modulation** - the process of combining the message signal with the carrier signal that causes the message signal to vary a characteristic of the carrier signal.
- **Demodulation** - the process of recovering or detecting the message signal from the modulated carrier frequency.
- **Amplitude Modulation (AM)** - the process of combining the message signal with the carrier signal and the two sidebands: the lower sideband and the upper sideband.
- **Frequency Modulation (FM)** - the process of combining the message signal with the carrier signal that causes the message signal to vary the frequency of the carrier signal.
- **Phase Modulation (PM)** - the process of combining the message signal with the carrier signal that causes the message signal to vary the phase of the carrier signal.
- **Angle modulation** - the process of combining the message signal with the carrier signal that causes the message signal to vary the frequency and/or phase of the carrier signal.
- **Balanced modulator** - an amplitude modulator that can be adjusted to control the amount of modulation.
- **Double-Sideband (DSB)** - an amplitude modulated signal in which the carrier is suppressed, leaving only the two sidebands: the lower sideband and the upper sideband.
- **Mixer** - an electronic circuit that combines two frequencies.
- **Product detector** - a detector whose audio frequency output is equal to the product of the Beat Frequency Oscillator (BFO) and the RF signal inputs.
- **Phase detector** - an electronic circuit whose output varies with the phase differential of the two input signals.

- **Envelopes**- the waveform of the amplitude variations of an amplitude modulated signal.
- **Sidebands** - the frequency bands on each side of the carrier frequency that are formed during modulation; the sideband frequencies contain the intelligence of the message signal.
- **AM** - an amplitude modulated signal that contains the carrier signal and the two sidebands: the lower sideband and the upper sideband.
- **Bandwidth** - the frequency range, in hertz (Hz), between the upper and lower frequency limits.
- **Harmonics** - signals with frequencies that are an integral multiple of the fundamental frequency.
- **Beat Frequency Oscillator (BFO)** - an oscillator whose output frequency is approximately equal to the transmitter's carrier frequency and is input to a product detector

Chapter 2

Amplitude Modulation- Generation

Aim

To design and set-up an AM generator using BJT and measure the modulation index from the observed output waveform.

Theory

The transistor T_1 is configured as a common emitter amplifier. The RF carrier wave is given at the base through a coupling capacitor C_1 . The message signal used for modulation is the AF signal applied between the emitter resistance and the ground. The message signal modulates the envelope of the carrier which is obtained as output from the collector through a coupling capacitor C_3 .

The ratio of the maximum amplitude of the modulating signal voltage to that of the carrier voltage is termed as modulation index. This is represented as $m = \frac{V_m}{V_c}$.

Design

Design steps need to be verified

DC Biasing conditions: Choose BF194 which is a high frequency transistor. From its datasheet (See A.1) the various parameters can be obtained as:

Let the supply voltage be 60% of the maximum V_{ce} .

$$V_{cc} = 60\% \text{ of } V_{ce_{max}} = 12V \quad (2.1)$$

Let the collector current I_c be 10% of maximum rated value.

$$I_c = 3\% \text{ of } I_{cmax} = 1mA \quad (2.2)$$

In-order to fix the biasing point in the middle of load line, let V_{RC} be 40% of V_{cc} , V_{RE} be 10% of V_{cc} and V_{ce} be 50% of V_{cc} .

$$V_{RC} = 45\% \text{ of } V_{cc} = 5.4V \quad (2.3)$$

$$V_{RE} = 5\% \text{ of } V_{cc} = 0.6V \quad (2.4)$$

$$V_{ce} = 50\% \text{ of } V_{cc} = 6V \quad (2.5)$$

Design of Resistors:

$$R_C = \frac{V_{RC}}{I_c} = \frac{5.4V}{1mA} = 5.4k\Omega \quad (2.6)$$

$$R_E = \frac{V_{RE}}{I_e} = \frac{0.6V}{1mA} = 600\Omega \quad (2.7)$$

From the datasheet, hFE has a minimum value of 67.

$$I_b = \frac{I_c}{hFE} = \frac{1mA}{67} = 15\mu A \quad (2.8)$$

Assume the current through $R_1 = 10I_b$ and that through $R_2 = 9I_b$

$$V_{R2} = V_{be} + V_{RE} = 0.7 + 0.6V = 1.3V \quad (2.9)$$

Then

$$R_2 = \frac{V_{R2}}{9I_b} = \frac{1.2V}{9 \times 15 \times 10^{-6}} = 8.8k\Omega \quad (2.10)$$

and

$$R_1 = \frac{V_{R1}}{10I_b} = \frac{10.8V}{10 \times 15 \times 10^{-6}} = 72k\Omega \quad (2.11)$$

Based on these design equations use the standard resistor values of $R_1 = 22k\Omega$, $R_2 = 10k\Omega$, $R_c = 10k\Omega$, $R_e = 560\Omega$ and a load resistance of $R_L = 1k\Omega$. Use coupling capacitors $C_1 = 0.1\mu F$, $C_2 = 0.001\mu F$ and emitter by-pass capacitor $C_E = 0.01\mu F$.

Components and Equipments Required

Function Generators(2), CRO(2), Connection wires, Breadboard, Probes.

BF194 - High frequency bipolar junction transistor

22k Ω , 10k Ω (2), 560 Ω , 1k Ω - Resistors

0.1 μF , 0.01 μF , 0.001 μF - Capacitors

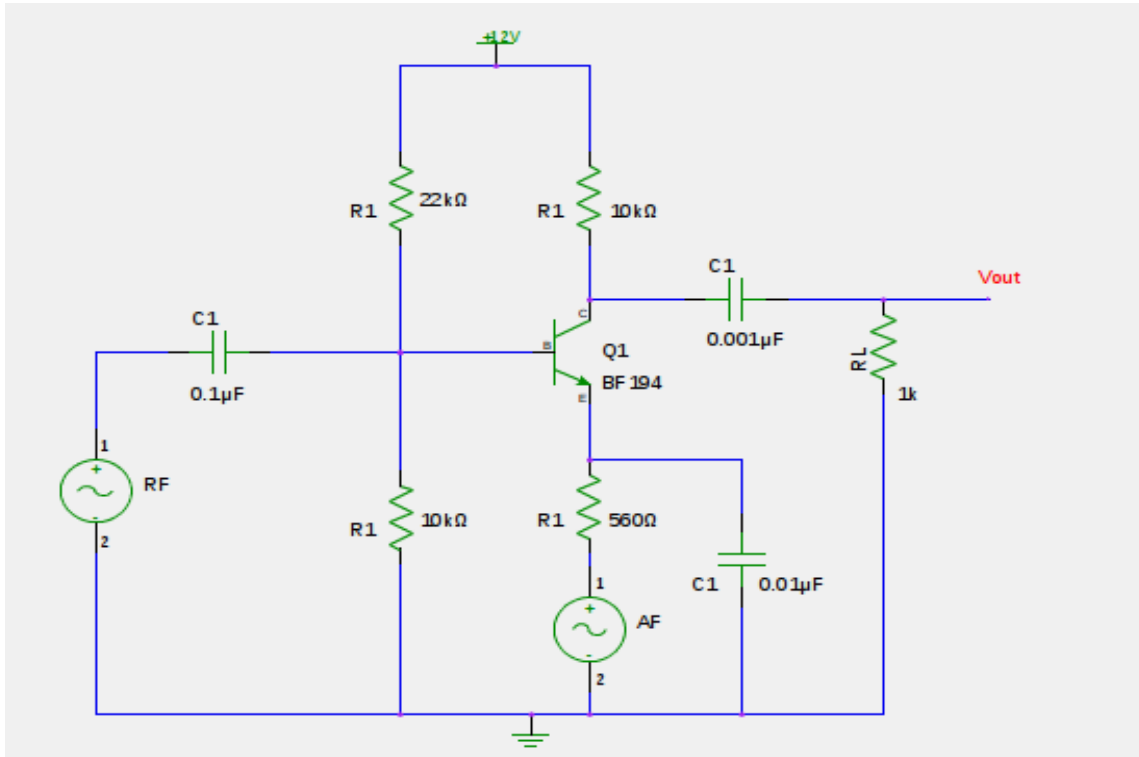


Figure 2.1: Circuit Diagram for Amplitude modulation using BJT

Circuit Diagram

Procedure

1. Set up the circuit after verifying the condition of components.
2. Feed AF modulating signal (say, $f_m = 1kHz$ and $E_m = 150mV$) and Rf carrier (say, $f_c = 70kHz$ and $E_c = 300mV$) using function generators.
3. Adjust amplitude and frequencies of the AF and RF signals and observe amplitude modulated waveform on the CRO.
4. Fix f_m and f_c . Note down E_{max} and E_{min} of the AM signal and calculate modulation index according to the formula ,

$$m = \frac{E_{max} - E_{min}}{E_{max} + E_{min}}. \quad (2.12)$$

Here E_{max} is the maximum of the positive envelope of the carrier and E_{min} is the minimum of the positive envelope of the carrier.

5. Repeat for different values of E_m and E_c . Observe the AM waveforms for different values of m .
6. Plot the waveforms on a graph sheet.
7. Fill in the observation column

Observation

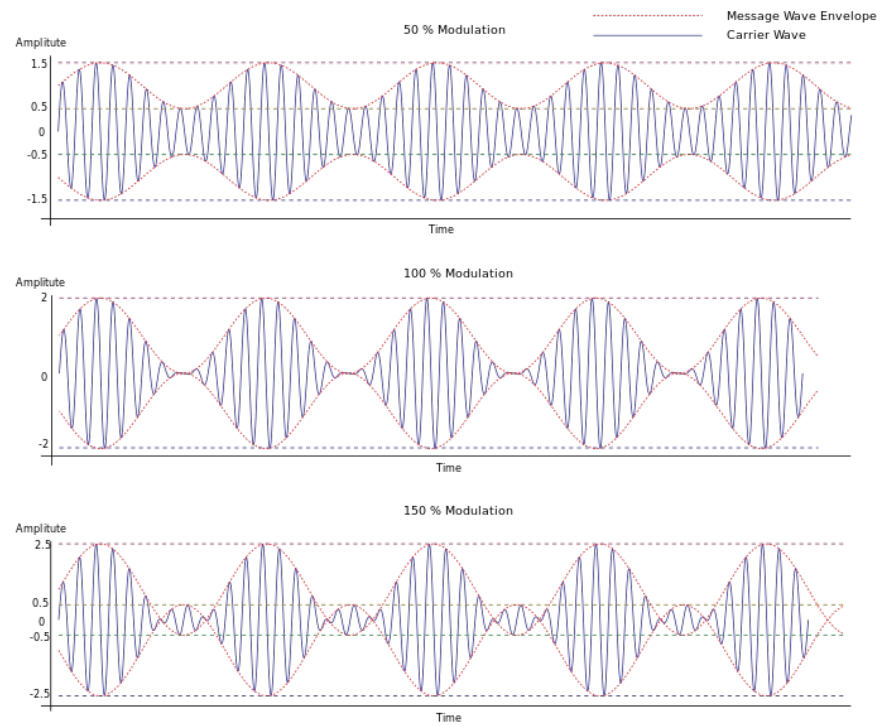


Figure 2.2: Effect of modulation index on AM

Fig 2.2 shows the effect of modulation index on the resultant AM wave¹

¹https://commons.wikimedia.org/wiki/File:Amplitude_Modulated_Wave-hm-64.svg

E_{min}	E_{max}	$m = \frac{E_{max} - E_{min}}{E_{max} + E_{min}}$

Result

Implemented the AM modulation circuit using BJT. The modulation index corresponding to $E_m = \text{---}$ and $E_c = \text{---}$ is : $m = \text{---}$.

Chapter 3

Amplitude Modulation - Detection

Aim

The experiment aims at designing an AM demodulator circuit and implementing it.

Theory

The AM signal is a high radio frequency carrier whose amplitude envelope represents a slow varying message signal, as can be seen in Fig. 2.2. The process of detecting the envelope and thus regaining the message signal from the modulated carrier wave is called AM demodulation.

It can be implemented by a simple diode envelope detector to eliminate the negative half of the carrier envelope followed by a simple RC filter to remove the high frequency carrier. The result will be the low frequency envelope which is the demodulated message.

A diode with low junction capacitance is used in the circuit as it has to rectify high frequency carrier. It offers low impedance at high frequency. The RC circuit used at the output of the diode acts as a filter. Its time constant is chosen wisely so that it is too slow to follow the high frequency of the carrier wave at the same time it is fast enough to follow the low frequency message envelope.

Design

Choose high frequency diode OA79.

The time period of the circuit must be much larger than the RF carrier frequency.

$$R_1 C_1 \gg T_c \quad (3.1)$$

$$R_1 C_1 \gg \frac{1}{f_c} = \frac{1}{2\pi\omega_c} \quad (3.2)$$

At the same time it should be smaller than the message bandwidth. ie.,

$$R_1 C_1 \ll \frac{1}{f_m} \quad (3.3)$$

Assuming $f_c = 100\text{kHz}$ ($T_c = .01\text{ms}$) and $f_m = 1\text{kHz}$ ($T_m = 1\text{ms}$), Let

$$R_1 C_1 = 10 T_c = 0.1\text{ms} \quad (3.4)$$

Let $C_1 = .01\mu\text{F}$

$$R_1 = \frac{.1\text{ms}}{C_1} \quad (3.5)$$

$$R_1 = \frac{.1\text{ms}}{0.01\mu\text{F}} = 10\text{k}\Omega. \quad (3.6)$$

Circuit Diagram

The circuit diagram for AM Demodulator using a simple diode detector is shown in Fig. 3.1.

Components and Equipments Required

CRO, Function Generators(2), Breadboard, Probes.

Diodes- OA79

Capacitor- $0.01\mu\text{F}$

Resistor- $10\text{k}\Omega$

Procedure

1. Make connections on the breadboard as per the circuit diagram.
2. Supply AM signal either from the signal generator or from the circuit designed in experiment Amplitude Modulation- Generation.
3. Connect the demodulated output to one channel of CRO along with the unmodulated signal on the other channel.

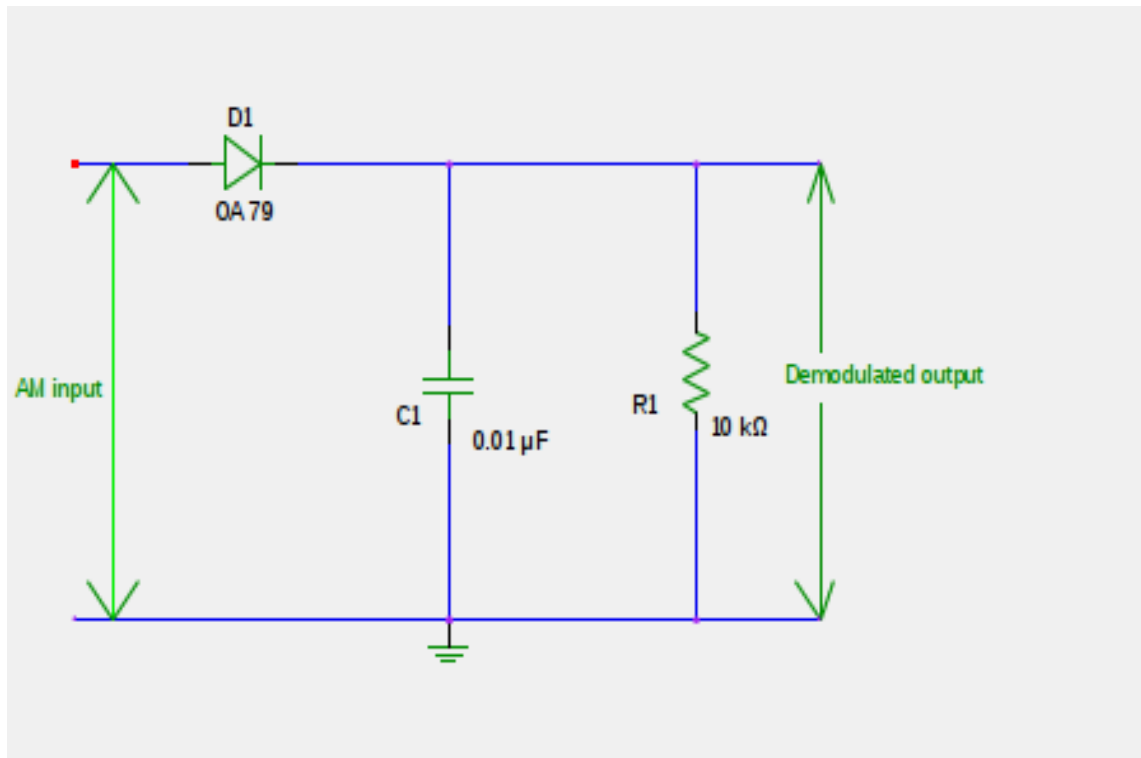


Figure 3.1: AM Demodulation-Simple Diode Detector

4. Observe the Modulated and demodulated waveforms and plot it on a graph sheet.

Observation

A model plot showing the expected result of the experiment is shown in the Fig.3.2

Result

AM demodulation circuit was implemented on breadboard and output was observed and plotted on a graph sheet.

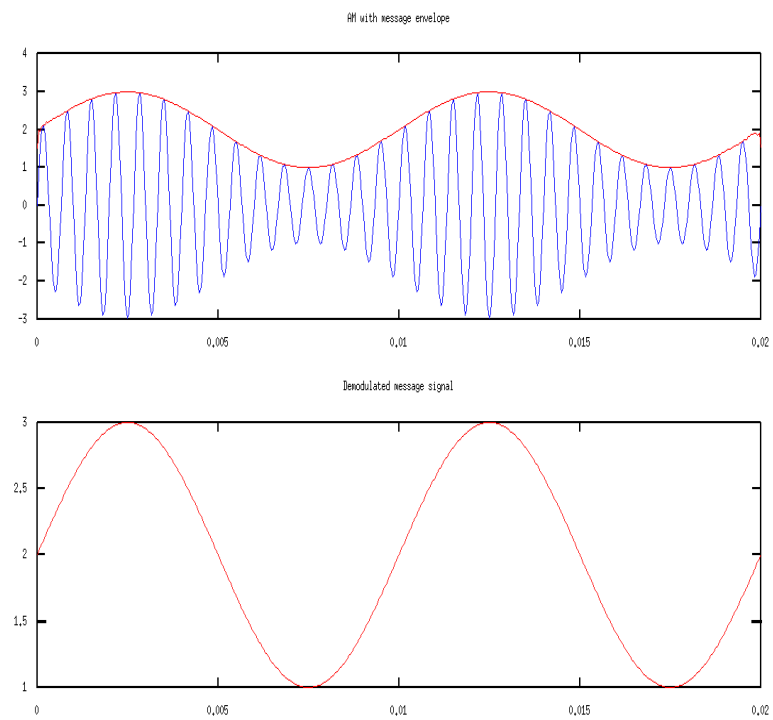


Figure 3.2: Modulated AM signal and Demodulated carrier

Chapter 4

Intermediate Frequency Tuned Amplifier

Aim

To design and implement a tuned intermediate frequency amplifier using BJT and IFT.

Theory

A tuned amplifier is same as a normal voltage amplifiers except that they are designed to amplify signals of a particular frequency and reject signals of all other frequencies.

A tuned load is to be inevitably used in the amplifier circuit to make the gain maximum at some particular frequency. The presence of tuned load eliminates the need for biasing BJT in the active region, because it can provide full sinusoidal swing of the output voltage even if the active element conducts only during a fraction of the sinusoidal cycle. The tuned circuit resonates at one frequency and so the unwanted frequencies are suppressed, and the wanted full signal (sine wave) is extracted by the tuned load.¹

The circuit here is a single tuned Class-C amplifier. An intermediate frequency transformer(IFT) is used as tuned load. IFT is tuned to standard 455 kHz audio frequency. (See A.2) **More on IFT may be addedd in appendix**

The Class-C operation reduces power dissipation in the active device. When the input signal is at the frequency of 455 kHz, the current pulses at that frequency are fed to the tuned load which makes them oscillate at that frequency. Thus full sinusoidal voltage waveform is generated across the load resistor.

¹http://en.wikipedia.org/wiki/Electronic_amplifier#Class_C

Design

Design equations need to be verified Let the required output be V_{pp} sine wave. Let the intermediate frequency for which the circuit is tuned is 455 kHz. Use high frequency transistor BF195.

$$I_c = 10\% \text{ of } I_{Cmax} = 1mA \quad (4.1)$$

Let V_{CC} be 20% more than the output, ie. 10V.

$$V_{CC} = 12V \quad (4.2)$$

For class C mode of operation set $V_{CE} = 10V$. Hence $V_{RE} = 2V$. Now the BJT is biased at cut-off.

$$V_{RE} = I_E \cdot R_E \quad (4.3)$$

$$I_E \approx I_C \quad (4.4)$$

Hence

$$I_E = 1mA \quad (4.5)$$

Thus

$$R_E = \frac{V_{RE}}{I_E} = \frac{2V}{1mA} = 2k\Omega \quad (4.6)$$

Design of Resistors R_1 and R_2

Since the transistor is in cut-off, $V_{BE} = 0V$. Hence,

$$V_{R2} = V_{BE} + V_{RE} = 0 + 2V = 2V \quad (4.7)$$

Let $I_2 = 9I_B$ and $I_1 = 10I_B$

$$I_B = \frac{I_C}{h_{FE}} = \frac{1mA}{67} = 14.9\mu A. \quad (4.8)$$

$$V_{R2} = R_2 I_2 \quad (4.9)$$

$$\therefore R_2 = \frac{V_{R2}}{I_2} = \frac{2}{9 \times 14.9\mu A} = 14.9k\Omega \approx 12k\Omega \quad (4.10)$$

$$V_{R1} = V_{CC} - V_{R2} = 12V - 2V = 10V \quad (4.11)$$

$$R_1 = \frac{V_{R1}}{10I_B} = \frac{10V}{10 \times 14.9\mu A} = 67k\Omega \quad (4.12)$$

Design of capacitors

The reactance of input coupling capacitor should be such that,

$$X_{C1} \leq \frac{R_{in}}{10} \quad (4.13)$$

$$R_{in} = R_1 || R_2 || h_{FE} r_e \quad (4.14)$$

Circuit Diagram

Procedure

Observation

Result

Chapter 5

Mixer Circuit using FET and BJT

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 6

Balanced Modulator for DSB-SC

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 7

FM generation - Reactance Modulator

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 8

FM Demodulation

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 9

PAM Generation and Demodulation

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 10

Intermediate Frequency Amplifier

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 11

FM Demodulation using PLL

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 12

AM generation and Demodulation

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Chapter 13

SSB generation and Demodulation

Aim

Theory

Design

Circuit Diagram

Procedure

Observation

Result

Appendix A

Quick Reference-Data on Components

A.1 BJT BF195/195

BF194/195 is a high frequency transistor. From its datasheet

Type Designator: BF194

Material of transistor: Si

Polarity: NPN

Maximum collector power dissipation (P_c), W: 0.25

Maximum collector-base voltage $|V_{cb}|$, V: 30

Maximum collector-emitter voltage $|V_{ce}|$, V: 20

Maximum emitter-base voltage $|V_{eb}|$, V: 5

Maximum collector current $|I_{cmax}|$, mA: 30

Forward current transfer ratio (hFE), min: 67

Pinout to be added

A.2 Intermediate Frequency Transformer

Bibliography

- [1] LABORATORY MANUAL COMMUNICATIONS LABORATORYEE 321,
CALIFORNIA STATE UNIVERSITY, LOS ANGELES Lab-Volt Systems, Inc